#12/Amdt C 3/14/02 VS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: **T. SATOH et al.**

Application No.: **09/809,181**

Filing Date: **March 16, 2001**

Title: **SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD FOR HIGH RELIABILITY AND PRODUCTION YIELD RATE WITH MINIMAL DAMAGE DUE TO APPLICATION OF MECHANICAL STRESS AND THERMAL STRESS (As Amended)**

Art Unit: **2815**

Examiner: **Jose R. Diaz**

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

March 5, 2002

Sir:

In response to the first Office Action (Paper No. 9) dated December 5, 2001, the following amendments and remarks are submitted in the above-identified application. Please amend the above-identified application as follows:

IN THE SUBSTITUTE SPECIFICATION

Paragraph beginning at line 7 of page 3 has been amended as follows:

On the other hand, recently, in association with wide spread use of portable information terminals, there is an increasing demand for miniaturization and high density assembly of a semiconductor device. Therefore, recently, a CSP (chip scale package) having a package size that is